

# DISCONTINUED

## ZXM64P035L3

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### 35V P-CHANNEL ENHANCEMENT MODE MOSFET

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#### SUMMARY

$V_{(BR)DSS} = -35V$ ;  $R_{DS(on)} = 0.075\Omega$ ;  $I_D = -12A$

#### DESCRIPTION

This new generation of high cell density planar MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

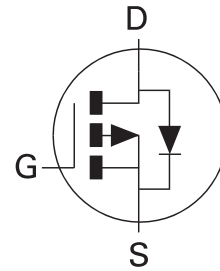


#### FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- TO220 package

#### APPLICATIONS

- 100W Class D Audio Output Stage
- Motor Control

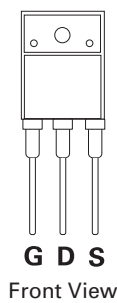


#### ORDERING INFORMATION

DEVICE	MULTIPLES
ZXM64P035L3	1000

#### DEVICE MARKING

- ZXM6  
4P035



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### ABSOLUTE MAXIMUM RATING

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DSS}$	-35	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current ( $V_{GS} = -10V$ ; $T_C = 25^\circ C$ )(a) ( $V_{GS} = -10V$ ; $T_A = 25^\circ C$ )(b)	$I_D$	-12 -3.3	A
Pulsed Drain Current (b)	$I_{DM}$	-19	A
Continuous Source Current (Body Diode) (b)	$I_S$	-2.3	A
Pulsed Source Current (Body Diode)(b)	$I_{SM}$	-19	A
Power Dissipation at $T_A = 25^\circ C$ (a) Linear Derating Factor	$P_D$	20 160	W mW/ $^\circ C$
Power Dissipation at $T_A = 25^\circ C$ (b) Linear Derating Factor	$P_D$	1.5 12	W mW/ $^\circ C$
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ C$

### THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Case (a)	$R_{\theta JC}$	6.25	$^\circ C/W$
Junction to Ambient (b)	$R_{\theta JA}$	83.3	$^\circ C/W$

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### ELECTRICAL CHARACTERISTICS (at $T_A = 25^\circ\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
<b>STATIC</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	-35			V	$I_D = -250\mu\text{A}, V_{GS} = 0\text{V}$
Zero Gate Voltage Drain Current	$I_{DSS}$			-1	$\mu\text{A}$	$V_{DS} = -35\text{V}, V_{GS} = 0\text{V}$
Gate-Body Leakage	$I_{GSS}$			$\pm 100$	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	-1.0			V	$I_D = -250\mu\text{A}, V_{DS} = V_{GS}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$			0.075 0.105	$\Omega$	$V_{GS} = -10\text{V}, I_D = -2.4\text{A}$ $V_{GS} = -4.5\text{V}, I_D = -1.2\text{A}$
Forward Transconductance (1)(3)	$g_{fs}$	2.3			S	$V_{DS} = -10\text{V}, I_D = -1.2\text{A}$
<b>DYNAMIC (3)</b>						
Input Capacitance	$C_{iss}$		825		pF	$V_{DS} = -25\text{V}, V_{GS} = 0\text{V},$ $f = 1\text{MHz}$
Output Capacitance	$C_{oss}$		250		pF	
Reverse Transfer Capacitance	$C_{rss}$		80		pF	
<b>SWITCHING(2) (3)</b>						
Turn-On Delay Time	$t_{d(on)}$		4.4		ns	$V_{DD} = -15\text{V}, I_D = -2.4\text{A}$ $R_G = 6.0\Omega, V_{GS} = -10\text{V}$
Rise Time	$t_r$		6.2		ns	
Turn-Off Delay Time	$t_{d(off)}$		40		ns	
Fall Time	$t_f$		29.2		ns	
Total Gate Charge	$Q_g$			46	nC	$V_{DS} = -24\text{V}, V_{GS} = -10\text{V},$ $I_D = -2.4\text{A}$
Gate-Source Charge	$Q_{gs}$			9	nC	
Gate-Drain Charge	$Q_{gd}$			11.5	nC	
<b>SOURCE-DRAIN DIODE</b>						
Diode Forward Voltage (1)	$V_{SD}$			-0.95	V	$T_J = 25^\circ\text{C}, I_S = -2.4\text{A},$ $V_{GS} = 0\text{V}$
Reverse Recovery Time (3)	$t_{rr}$		30.2		ns	$T_J = 25^\circ\text{C}, I_F = -2.4\text{A},$ $di/dt = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge (3)	$Q_{rr}$		27.8		nC	

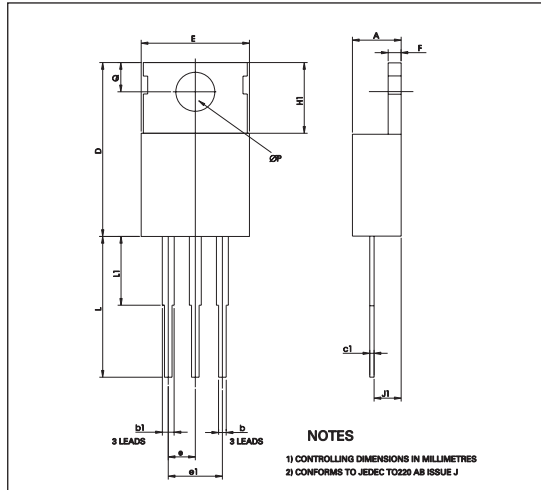
#### NOTES

- (1) Measured under pulsed conditions. Width=300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$ .
- (2) Switching characteristics are independent of operating junction temperature.
- (3) For design aid only, not subject to production testing.

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### Package Outline



### Package Dimensions

DIM	Millimetres		Inches	
	Min	Max	Min	Max
A	3.56	4.82	0.140	0.189
b	0.38	1.01	0.015	0.040
b1	1.15	1.77	0.045	0.070
c1	0.41	0.50	0.016	0.020
D	14.23	16.51	0.560	0.650
E	9.66	10.66	0.380	0.419
e	2.29	2.79	0.090	0.110
e1	4.83	5.33	0.190	0.210
F	0.51	1.39	0.20	0.055
H1	5.58	6.85	0.230	0.270
J1	2.04	2.92	0.080	0.115
L	12.70	14.73	0.500	0.580
L1	—	6.35	—	0.250
ØP	3.54	4.08	0.139	0.160
Q	2.54	3.42	0.100	0.134

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